

## Notice of R ferences Cited

Application/Control No. 09/771,556	Applicant(s)/Pate Reexamination TANINO ET AL.	nt Under
Examiner	Art Unit	
Robert M Kun mund	1765	Page 1 of 1

## U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-6,153,165	11-2000	Tanino	423/345
	В	US-6,217,842	04-2001	Tanino	117/951
	С	US-6,153,166	11-2000	Tanino	117/4
	D	US-6,143,267	11-2000	Tanino	117/4
<u></u>	Е	US-6,187,279	02-2001	Tanino et al	117/7
	F	US-			11111
	G	US-			
	Н	US-			
	1	US-			
	J	US-			
	к	US-			
	L	US-			
	М	US-			

## FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	0					
	Р		<i>j</i> *			
	Q		,			
T	R					
	s					
	Т					

## **NON-PATENT DOCUMENTS**

		TOTAL ATENI DOCUMENTS
*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Luo et al., "Localized epitaxial growth of hexagonal and cubic SiC films on Si by vacuum annealing", Applied Physics Letters vol 69(7) August 12, 1996 pages 916-918
	v	
	w	
	х	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).) Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.